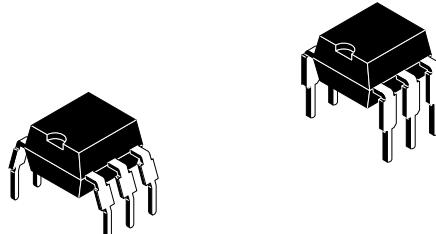


Optocoupler with Phototransistor Output

Description

The CQY80N(G) series consist of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 6-lead plastic dual inline package. The elements are mounted on one leadframe using a **coplanar technique**, providing a fixed distance between input and output for highest safety requirements.



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Applications

Circuits for safe protective separation against electrical shock according to safety class II (reinforced isolation):

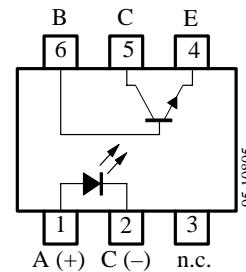
- For appl. class I – IV at mains voltage ≤ 300 V
- For appl. class I – III at mains voltage ≤ 600 V according to VDE 0884, table 2, suitable for:

Switch-mode power supplies, line receiver, computer peripheral interface, microprocessor system interface.

VDE Standards

These couplers perform safety functions according to the following equipment standards:

- **VDE 0884**
Optocoupler for electrical safety requirements
- **IEC 950/EN 60950**
Office machines (applied for reinforced isolation for mains voltage ≤ 400 V_{RMS})
- **VDE 0804**
Telecommunication apparatus and data processing
- **IEC 65**
Safety for mains-operated electronic and related household apparatus



Order Instruction

Ordering Code	CTR Ranking	Remarks
CQY80N	> 50%	
CQY80NG ¹⁾	> 50%	
1) G = Leadform 10.16 mm; G is not market on the body		



Features

Approvals:

- **BSI:** BS EN 41003, BS EN 60095 (BS 415),
BS EN 60950 (BS 7002),
Certificate number 7081 and 7402
- **FIMKO (SETI):** EN 60950,
Certificate number 12399
- **Underwriters Laboratory (UL) 1577 recognized,**
file number E-76222
- **VDE 0884,** Certificate number 94778

VDE 0884 related features:

- Rated impulse voltage (transient overvoltage)
 $V_{IOTM} = 6 \text{ kV peak}$
- Isolation test voltage
(partial discharge test voltage) $V_{pd} = 1.6 \text{ kV}$
- Rated isolation voltage (RMS includes DC)
 $V_{IOWM} = 600 \text{ V}_{\text{RMS}}$ (848 V peak)

- Rated recurring peak voltage (repetitive)
 $V_{IORM} = 600 \text{ V}_{\text{RMS}}$
- Creepage current resistance according to
VDE 0303/IEC 112
Comparative Tracking Index: **CTI = 275**
- Thickness through insulation $\geq 0.75 \text{ mm}$

General features:

- Isolation materials according to UL94-VO
- Pollution degree 2
(DIN/VDE 0110 / resp. IEC 664)
- Climatic classification 55/100/21 (IEC 68 part 1)
- Special construction:
Therefore, extra low coupling capacity of
typical 0.3 pF, high **Common Mode Rejection**
- Low temperature coefficient of CTR
- CTR > 50%
- Coupling System A

Absolute Maximum Ratings

Input (Emitter)

Parameter	Test Conditions	Symbol	Value	Unit
Reverse voltage		V_R	5	V
Forward current		I_F	60	mA
Forward surge current	$t_p \leq 10 \mu\text{s}$	I_{FSM}	1.5	A
Power dissipation	$T_{amb} \leq 25^\circ\text{C}$	P_V	100	mW
Junction temperature		T_j	125	°C

Output (Detector)

Parameter	Test Conditions	Symbol	Value	Unit
Collector emitter voltage		V_{CEO}	32	V
Emitter collector voltage		V_{ECO}	7	V
Collector current		I_C	50	mA
Collector peak current	$t_p/T = 0.5, t_p \leq 10 \text{ ms}$	I_{CM}	100	mA
Power dissipation	$T_{amb} \leq 25^\circ\text{C}$	P_V	150	mW
Junction temperature		T_j	125	°C

Coupler

Parameter	Test Conditions	Symbol	Value	Unit
Isolation test voltage (RMS)	$t = 1 \text{ min}$	V_{IO}	3.75	kV
Total power dissipation	$T_{amb} \leq 25^\circ\text{C}$	P_{tot}	250	mW
Ambient temperature range		T_{amb}	-55 to +100	°C
Storage temperature range		T_{stg}	-55 to +125	°C
Soldering temperature	2 mm from case, $t \leq 10 \text{ s}$	T_{sd}	260	°C

Electrical Characteristics ($T_{amb} = 25^\circ C$)**Input (Emitter)**

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Forward voltage	$I_F = 50 \text{ mA}$	V_F		1.25	1.6	V
Junction capacitance	$V_R = 0, f = 1 \text{ MHz}$	C_j		50		pF

Output (Detector)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Collector emitter voltage	$I_C = 1 \text{ mA}$	V_{CEO}	32			V
Emitter collector voltage	$I_E = 100 \mu\text{A}$	V_{ECO}	7			V
Collector emitter cut-off current	$V_{CE} = 20 \text{ V}, I_f = 0, E = 0$	I_{CEO}		10	200	nA

Coupler

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Collector emitter saturation voltage	$I_F = 10 \text{ mA}, I_C = 1 \text{ mA}$	V_{CEsat}			0.3	V
Cut-off frequency	$V_{CE} = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 100 \Omega$	f_c		110		kHz
Coupling capacitance	$f = 1 \text{ MHz}$	C_k		0.3		pF

Current Transfer Ratio (CTR)

Parameter	Test Conditions	Type	Symbol	Min.	Typ.	Max.	Unit
I_C/I_F	$V_{CE} = 5 \text{ V}, I_F = 10 \text{ mA}$	CQY80N, CQY80NG	CTR	0.5	0.9		